

Improving Optical and Electrical Characteristics of GaN Films via 3D Island to 2D Growth Mode Transition Using Molecular Beam Epitaxy

Supplementary Materials

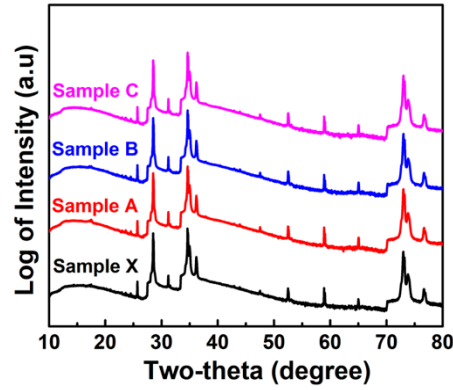


Figure S1: The 2-theta diffraction patterns of MBE-grown GaN films and the MOCVD GaN/Si template.

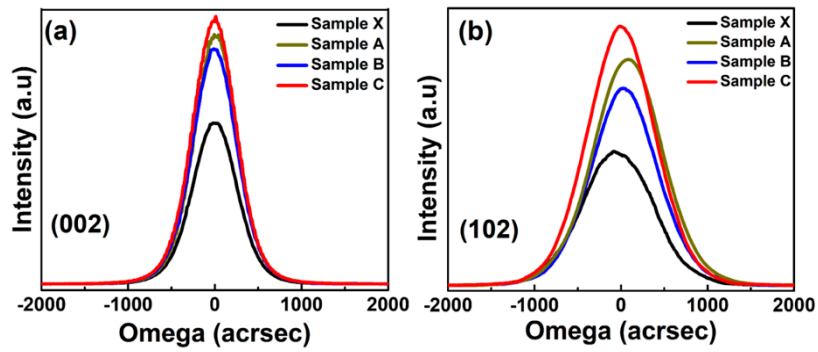


Figure S2: X-ray rocking curves of all GaN films scanned on (a) (002) and (b) (102) reflections.